TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL JUNCTION TYPE

2 S K 3 6 8

AUDIO FREQUENCY AND HIGH VOLTAGE AMPLIFIER APPLICATIONS CONSTANT CURRENT APPLICATIONS

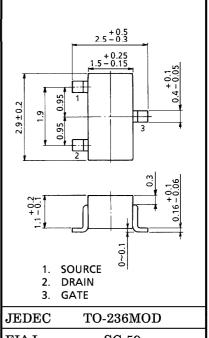
• High Breakdown Voltage: VGDS = -100V (Min.)

• High Input Impedance : $I_{GSS} = -1.0 \text{nA} \text{ (Max.) (V}_{GS} = -80 \text{V)}$

Small Package

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	v_{GDS}	-100	V
Gate Current	$I_{\mathbf{G}}$	10	mA
Drain Power Dissipation	P_{D}	150	mW
Junction Temperature	T_{j}	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

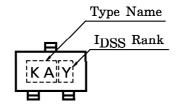


Unit in mm

JEDEC TO-236MOD
EIAJ SC-59
TOSHIBA 2-3F1B

Weight: 0.012g

Marking

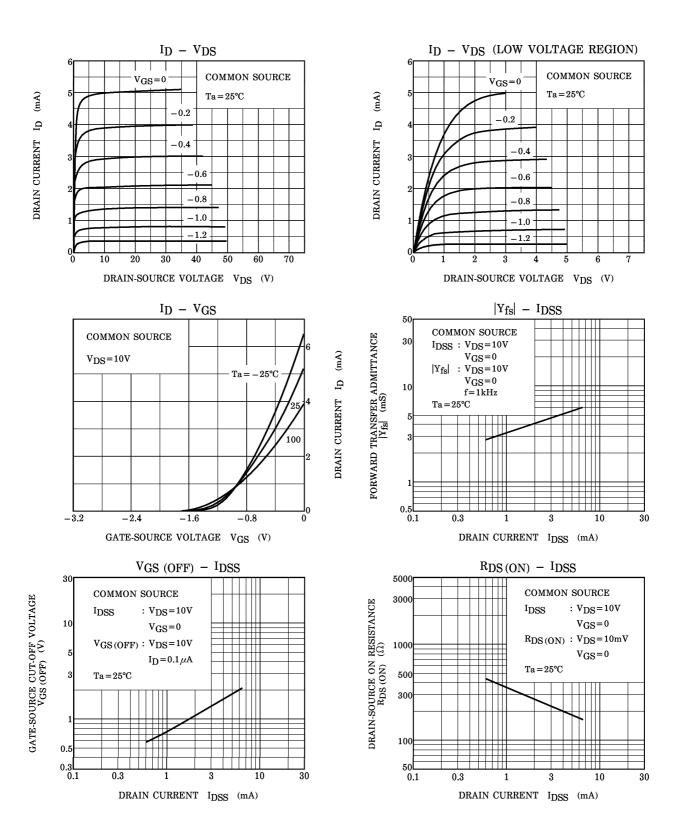


ELECTRICAL CHARACTERISTICS (Ta = 25°C)

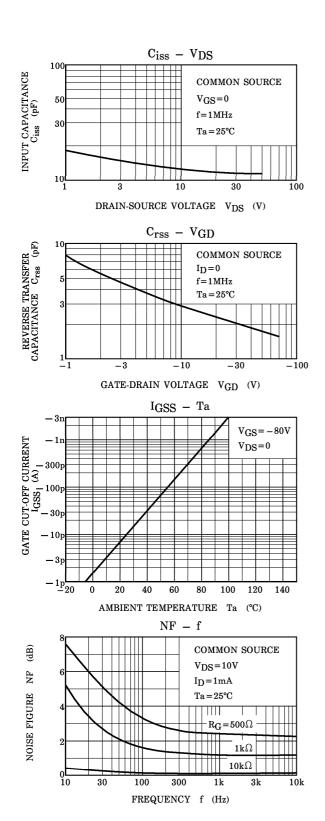
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Cut-off Current	IGSS	$V_{GS} = -80V, V_{DS} = 0$	_		-1.0	nA
Gate-Drain Breakdown Voltage	V _(BR) GDS	$V_{DS} = 0, I_G = -100 \mu A$	-100	_	_	V
Drain Current	I _{DSS} (Note)	$V_{DS} = 10V, V_{GS} = 0$	0.6		6.5	mA
Gate-Source Cut-off Voltage	V _{GS (OFF)}	$V_{DS} = 10V, I_{D} = 0.1 \mu A$	-0.4	_	-3.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V, V_{GS} = 0, f = 1kHz$	1.5	4.6	_	mS
Input Capacitance	$\mathrm{c}_{\mathrm{iss}}$	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$	_	13	_	pF
Reverse Transfer Capacitance	$\mathrm{c}_{\mathrm{rss}}$	$V_{ m DG} = 10 V, I_{ m D} = 0, f = 1 MHz$	_	3	_	pF
Noise Figure	NF	$V_{DS}=10V, V_{GS}=0 \\ R_{G}=100k\Omega, f=100Hz$	_	0.5	_	dB

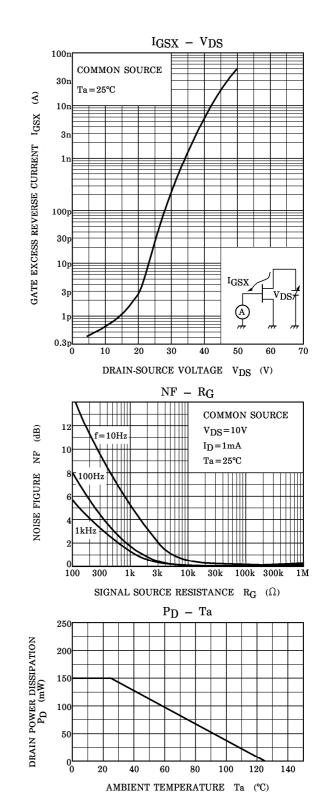
Note: IDSS Classification $O: 0.6\sim1.4\text{mA}, Y: 1.2\sim3.0\text{mA}, GR(G): 2.6\sim6.5\text{mA}$

1 2001-05-31



2 2001-05-31





3 2001-05-31

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